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## Advance Information

# **Complementary Silicon Power Transistors**

The MJ15011 and MJ15012 are PowerBase power transistors designed for high-power audio, disk head positioners, and other linear applications. These devices can also be used in power switching circuits such as relay or solenoid drivers, dc-to-dc converters or inverters.

- High Safe Operating Area (100% Tested)
   1.2 A @ 100 V
- · Completely Characterized for Linear Operation
- High DC Current Gain and Low Saturation Voltage hFE = 20 (Min) @ 2 A, 2 V VCE(sat) = 2.5 V (Max) @ IC = 4 A, IB = 0.4 A
- For Low Distortion Complementary Designs

## MJ15011\* PNP MJ15012\*

\*Motorola Preferred Device

10 AMPERE COMPLEMENTARY POWER TRANSISTORS 250 VOLTS 200 WATTS



(TO-3)

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	VCEO	250	Vdc
Collector-Emitter Voltage	VCEX	250	Vdc
Emitter–Base Voltage	VEB	5	Vdc
Collector Current — Continuous — Peak (1)	I <sub>C</sub>	10 15	Adc
Base Current — Continuous — Peak (1)	I <sub>B</sub>	2 5	Adc
Emitter Current — Continuous — Peak (1)	I <sub>E</sub>	12 20	Adc
Total Power Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	PD	200 1.14	Watts W/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-65 to +200	°C

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	R <sub>0</sub> JC	0.875	°C/W
Maximum Lead Temperature for Soldering Purposes	TL	265	°C

(1) Pulse Test: Pulse Width = 5 ms, Duty Cycle  $\leq$  10%.

NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

**Quality Semi-Conductors** 

### MJ15011 MJ15012

## **ELECTRICAL CHARACTERISTICS** ( $T_C = 25$ °C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Breakdown Voltage (1) (IC = 100 mA)	V <sub>(BR)CEO</sub>	250	_	Vdc
Collector Cutoff Current (VCE = 200 Vdc)	ICEO	_	1	mAdc
Collector Cutoff Current (V <sub>CE</sub> = 250 Vdc, V <sub>BE(off)</sub> = 15 Vdc)	ICEX	_	500	μAdc
Emitter Cutoff Current (V <sub>BE</sub> = 5 Vdc)	lEBO		500	μAdc
ON CHARACTERISTICS (1)				_
DC Current Gain (IC = 2 Adc, VCE = 2 Vdc) (IC = 4 Adc, VCE = 2 Vdc)	hFE	20 5	100	_
Collector–Emitter Saturation Voltage (IC = 2 Adc, I <sub>B</sub> = 0.2 Adc) (IC = 4 Adc, I <sub>B</sub> = 0.4 Adc)	VCE(sat)	_	0.8 2.5	Vdc
Base–Emitter On Voltage (IC = 4 Adc, V <sub>CE</sub> = 2 Vdc)	V <sub>BE(on)</sub>	_	2	Vdc
DYNAMIC CHARACTERISTICS				
Output Capacitance (V <sub>CB</sub> = 10 Vdc, f = 1 MHz)	C <sub>ob</sub>	_	750	pF
SECOND BREAKDOWN				-
Second Breakdown Collector Current with Base Forward Biased (VCE = 40 Vdc, t = 0.5 s) (VCE = 100 Vdc, t = 0.5 s)	<sup> </sup> S/b	5 1.4		Adc

<sup>(1)</sup> Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2%.

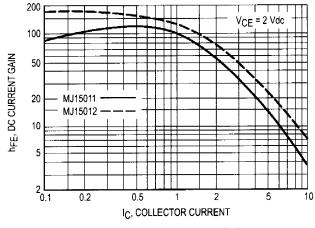


Figure 1. DC Current Gain

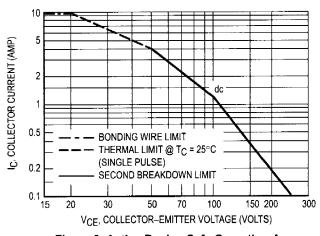
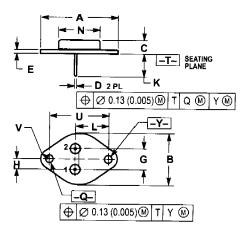


Figure 2. Active Region Safe Operating Area



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. ALL RULES AND NOTES ASSOCIATED WITH REFERENCED TO-204AA OUTLINE SHALL APPLY.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
A_	1.550 REF		39.37 REF		
В		1.050		26.67	
C	0.250	0.335	6.35	8.51	
D	0.038	0.043	0.97	1.09	
E	0.055	0.070	1.40	1.77	
G	0.430 BSC		10.92 BSC		
Н	0.215 BSC		5.46 BSC		
K	0.440	0.480	11.18	12.19	
L	0.665 BSC		16.89 BSC		
N		0.830		21.08	
Q	0.151	0.165	3.84	4.19	
U	1.187 BSC		30.15 BSC		
V	0.131	0.188	3.33	4.77	

STYLE 1: PIN 1. BASE 2. EMITTER CASE: COLLECTOR